

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

SCH1335 — General-Purpose Switching Device Applications

Features

- 1.8V drive
- · Halogen free compliance

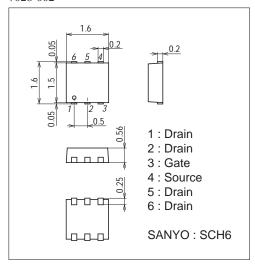
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-12	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	ID		-2.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-10	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² x0.8mm)	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7028-002



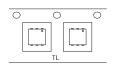
Product & Package Information

• Package : SCH6

• JEITA, JEDEC :-

• Minimum Packing Quantity : 5,000 pcs./reel

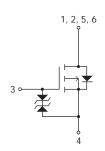
Packing Type: TL



Marking



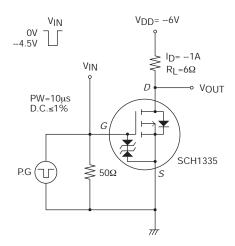
Electrical Connection

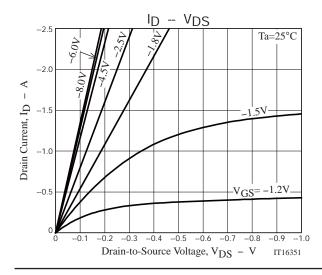


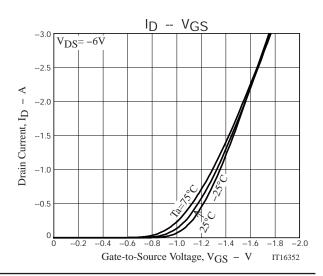
Electrical Characteristics at Ta=25°C

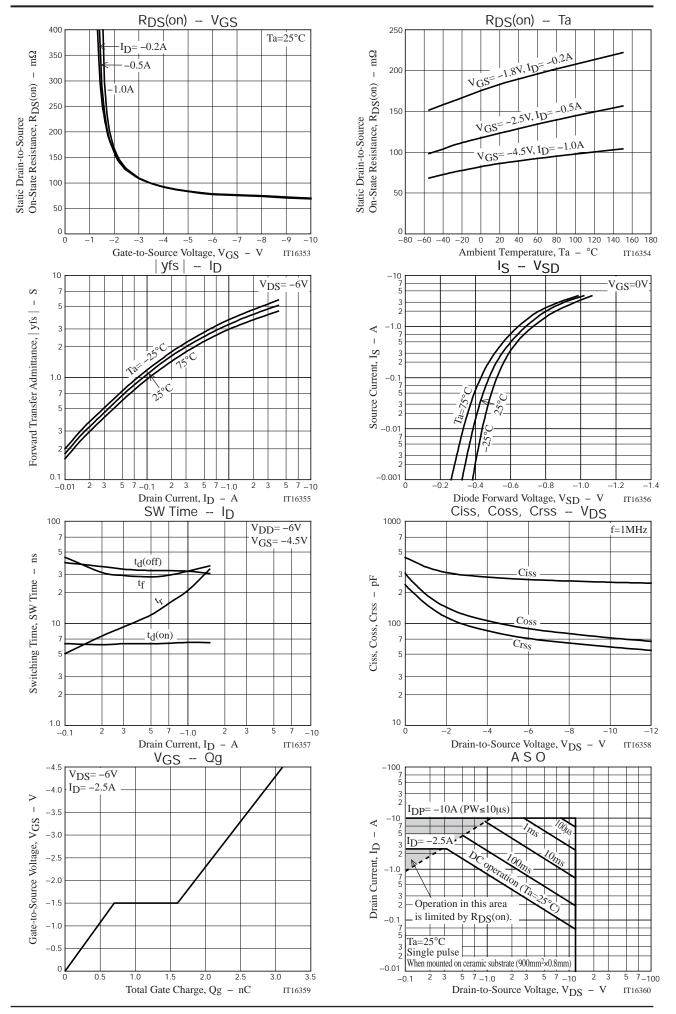
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-12			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V			-10	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =-6V, I _D =-1mA	-0.4		-1.3	V
Forward Transfer Admittance	yfs	V _D S=-6V, I _D =-1A		3.3		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =-1A, V _G S=-4.5V		86	112	mΩ
	R _{DS} (on)2	I _D =-0.5A, V _G S=-2.5V		125	175	mΩ
	R _{DS} (on)3	I _D =-0.2A, V _G S=-1.8V		185	285	mΩ
Input Capacitance	Ciss	V _{DS} =-6V, f=1MHz		270		pF
Output Capacitance	Coss	V _{DS} =-6V, f=1MHz		90		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-6V, f=1MHz		72		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit.		6.5		ns
Rise Time	tr	See specified Test Circuit.		21		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		33		ns
Fall Time	t _f	See specified Test Circuit.		33		ns
Total Gate Charge	Qg	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-2.5A		3.1		nC
Gate-to-Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-2.5A		0.7		nC
Gate-to-Drain "Miller" Charge	Qgd	V _D S=-6V, V _G S=-4.5V, I _D =-2.5A		0.9		nC
Diode Forward Voltage	V _{SD}	I _S =-2.5A, V _{GS} =0V		-0.84	-1.2	V

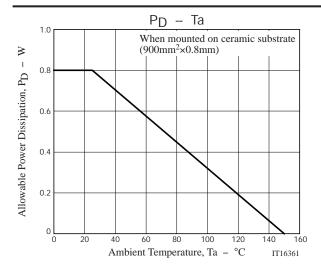
Switching Time Test Circuit











Note on usage: Since the SCH1335 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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